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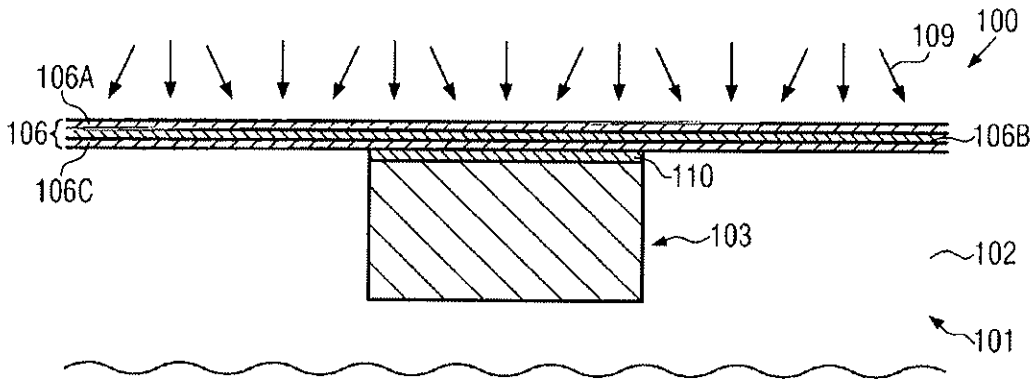


FIG. 1h

(57) **Abstract:** By forming an aluminum nitride layer (106) by a self-limiting process sequence, the interface characteristics of a copper-based metallization layer may be significantly enhanced while nevertheless maintaining the overall permittivity of the layer stack at a lower level.

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